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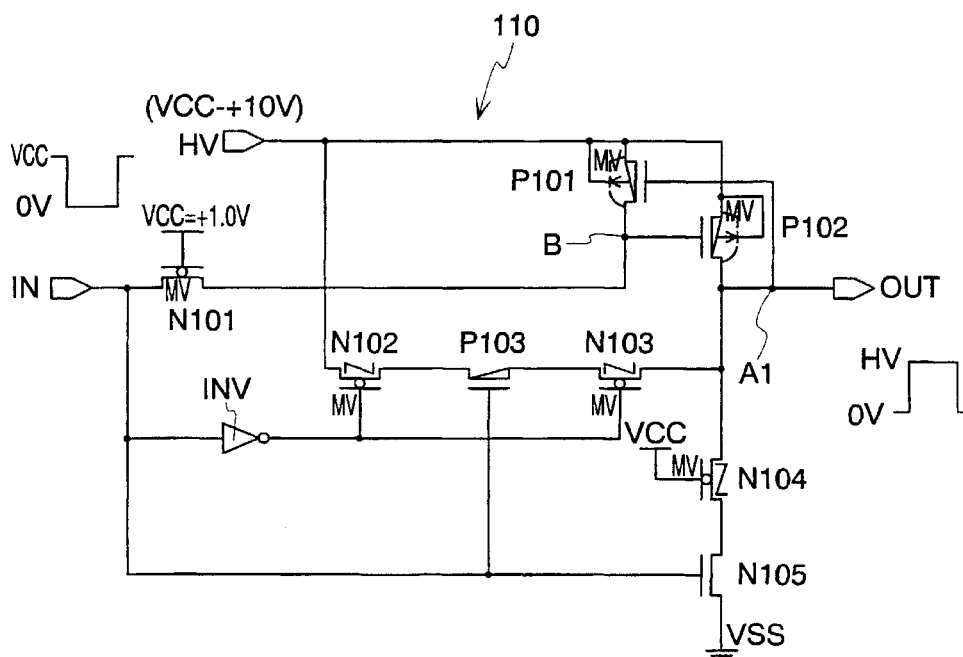
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(54) Title: LEVEL-SHIFTER FOR EXTREMELY LOW POWER SUPPLY



(57) Abstract: An improved level shifter circuit is provided which is designed for use with an extremely low power supply voltage. The level shifter circuit includes a fourth NMOS transistor (N102), a third PMOS transistor (P103), and a fifth NMOS transistor (N103) connected in series and interconnected between the high voltage and the output terminal. As a result, the high voltage will still be passed to the output terminal when the high voltage is lowered to be equal to the low power supply voltage.



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